

Multilayer Power Inductor

CIG32H2R2MNE (3225/ EIA 1210)

APPLICATION

Mobile phones, DSC, DVC, PDA etc. for DC-DC Converter

FEATURES

- High Current Type
- · Low DC resistance
- Magnetically shielded structure
- Free of all RoHS-regulated substances
- · Monolithic structure for high reliability



RECOMMENDED LAND PATTERN





DESCRIPTION

Part no.	Size	Inductance	DC	Rated Current (A)*1	Rated Current (A)*2
	(inch/mm)	(uH)@1MHz	Resistance(Ω)	Тур.	Max.
CIG32H2R2MNE	1210/3225	2.2±20%	0.125±25 %	2.90	1.60

**Operating temperature range: -40 to +125°C (Including self-temperature rise)
**Test equipment: Agilent :E4991A+16092A

CHARACTERISTIC DATA



2) DC Bias characteristics (Typ.)





CI G 32 H 2R2 M N E (1) (2) (3) (4) (5) (6) (7) (8)

- (1) Chip Inductor
- (3) Dimension
- (5) Inductance (2R2:2.2uH)

- (2) Power Inductor
- (4) Product Series (H:High Current Type)

FLOW SOLDERING

- (6) Tolerance (M:±20%)
- (7) Thickness option(N:Standard, A:Thinner than standard, B:Thicker than standard)
- (8) Packaging(C:paper tape, E:embossed tape)

RECOMMENDED SOLDERING CONDITION



REFLOW SOLDERING

PACKAGING

Packaging Style	Quantity(pcs/reel)	
Embossed Taping	2,500	

Any data in this sheet are subject to change, modify or discontinue without notice. The data sheets include the typical data for design reference only. If there is any question regarding the data sheets, please contact our sales personnel or application engineers.